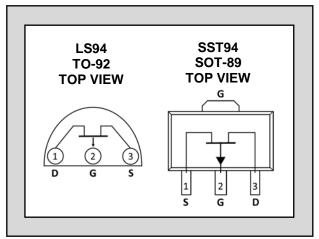


Over 30 Years of Quality Through Innovation

LS94, SST94

GENERAL PURPOSE SINGLE P-CHANNEL JFET

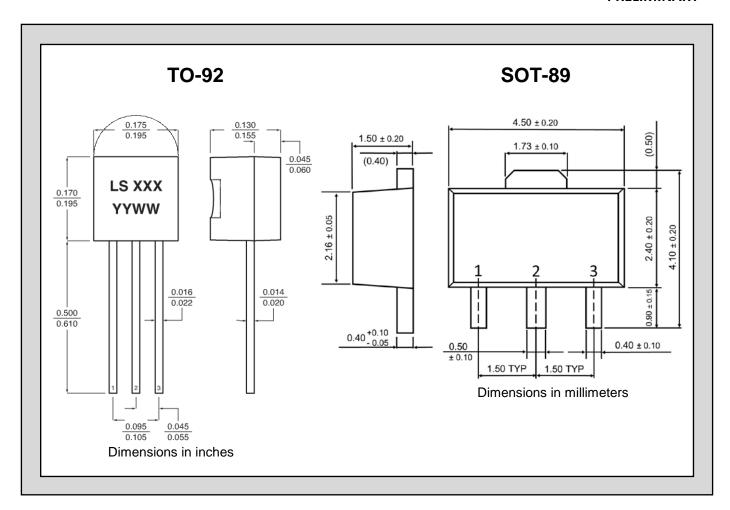
FEATURES				
HIGH GAIN	$G_{fs} = 22mS (typ)$			
HIGH INPUT IMPEDANCE	$I_G = 1.0 nA$			
LOW CAPACITANCE	$C_{RSS} = 32pF$			
ABSOLUTE MAXIMUM RATINGS¹ @ 25 °C (unless otherwise stated)				
Maximum Temperatures				
Storage Temperature	-55 to +150°C			
Junction Operating Temperature	-55 to +135°C			
Maximum Power Dissipation				
Continuous Power Dissipation	400mW			
Maximum Currents				
Gate Forward Current	$I_{G(F)} = -10mA$			
Maximum Voltages				
Gate to Drain Voltage	$V_{GD} = 25V$			
Gate to Source Voltage	V _{GS} = 25V			



^{*} For equivalent N-Channel, see LSK190

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
BV _{GDS}	Gate to Drain Breakdown Voltage	25			V	$V_{DS} = 0V, I_G = 100 \mu A$
V _{GS(OFF)}	Gate to Source Pinch-off Voltage	0.15		2	V	$V_{DS} = -10V$, $I_{D} = -0.1\mu A$
IDSS	Drain to Source Saturation Current ²	-2.6		-30	mA	$V_{DS} = -10V$, $V_{GS} = 0V$
I _G	Gate Operating Current		50		pА	$V_{DG} = -10V, I_{D} = -1mA$
Igss	Gate to Source Leakage Current			1	nA	$V_{GS} = 25V$, $V_{DS} = 0V$
G _{fss}	Full Conductance Transconductance	8	22		mS	$V_{DS} = -10V$, $V_{GS} = 0V$, $f = 1kHz$
R _{DS(on)}	Drain to Source on Resistance		75	150	Ω	$V_{GS} = 0V$, $I_D = -1mA$
Ciss	Common Source Input Capacitance		105		nE	$V_{DS} = -10V$, $V_{GS} = 0V$, $f = 1MHz$
C _{RSS}	Common Source Reverse Transfer Cap.		32		pF	$V_{DS} = -10V$, $I_{D} = 0A$, $f = 1MHz$



NOTES:

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. Pulse test: PW \leq 300 μ S, Duty Cycle \leq 3%
- 3. All MIN/TYP/MAX Limits are absolute values. Negative signs indicate negative electrical polarity only.

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